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# FDPF16N50 / FDPF16N50T N-Channel UniFET™ MOSFET 500 V, 16 A, 380 mΩ

## Features

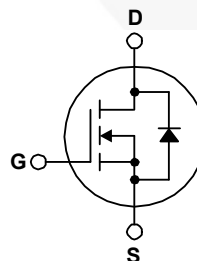
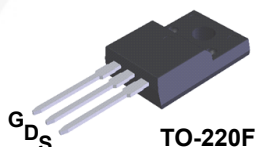
- $R_{DS(on)} = 380 \text{ m}\Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 8 \text{ A}$
- Low Gate Charge (Typ. 32 nC)
- Low  $C_{rss}$  (Typ. 20 pF)
- 100% Avalanche Tested

## Applications

- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

## Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



## Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol         | Parameter                                                                                                | FDPF16N50<br>FDPF16N50T | Unit                     |
|----------------|----------------------------------------------------------------------------------------------------------|-------------------------|--------------------------|
| $V_{DSS}$      | Drain-Source Voltage                                                                                     | 500                     | V                        |
| $I_D$          | Drain Current<br>- Continuous ( $T_C = 25^\circ\text{C}$ )<br>- Continuous ( $T_C = 100^\circ\text{C}$ ) | 16*<br>9.6*             | A<br>A                   |
| $I_{DM}$       | Drain Current - Pulsed (Note 1)                                                                          | 64*                     | A                        |
| $V_{GSS}$      | Gate-Source voltage                                                                                      | $\pm 30$                | V                        |
| $E_{AS}$       | Single Pulsed Avalanche Energy (Note 2)                                                                  | 780                     | mJ                       |
| $I_{AR}$       | Avalanche Current (Note 1)                                                                               | 16                      | A                        |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)                                                                     | 20                      | mJ                       |
| $dv/dt$        | Peak Diode Recovery $dv/dt$ (Note 3)                                                                     | 4.5                     | V/ns                     |
| $P_D$          | Power Dissipation ( $T_C = 25^\circ\text{C}$ )<br>- Derate above $25^\circ\text{C}$                      | 38.5<br>0.3             | W<br>W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                                                                  | -55 to +150             | $^\circ\text{C}$         |
| $T_L$          | Maximum Lead Temperature for Soldering,<br>1/8" from Case for 5 Seconds                                  | 300                     | $^\circ\text{C}$         |

\* Drain current limited by maximum junction temperature.

## Thermal Characteristics

| Symbol          | Parameter                                     | FDPF16N50<br>FDPF16N50T | Unit               |
|-----------------|-----------------------------------------------|-------------------------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max.    | 3.3                     | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 62.5                    | $^\circ\text{C/W}$ |

## Package Marking and Ordering Information

| Part Number | Top Mark   | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|------------|---------|----------------|-----------|------------|----------|
| FDPF16N50   | FDPF16N50  | TO-220F | Tube           | N/A       | N/A        | 50 units |
| FDPF16N50T  | FDPF16N50T | TO-220F | Tube           | N/A       | N/A        | 50 units |

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted.

| Symbol                                                 | Parameter                                             | Conditions                                                                                     | Min. | Typ. | Max     | Unit     |
|--------------------------------------------------------|-------------------------------------------------------|------------------------------------------------------------------------------------------------|------|------|---------|----------|
| Off Characteristics                                    |                                                       |                                                                                                |      |      |         |          |
| BV <sub>DSS</sub>                                      | Drain-Source Breakdown Voltage                        | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA                                                   | 500  | --   | --      | V        |
| ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>                   | Breakdown Voltage Temperature Coefficient             | I <sub>D</sub> = 250μA, Referenced to 25°C                                                     | --   | 0.5  | --      | V/°C     |
| I <sub>DSS</sub>                                       | Zero Gate Voltage Drain Current                       | V <sub>DS</sub> = 500V, V <sub>GS</sub> = 0V<br>V <sub>DS</sub> = 400V, T <sub>C</sub> = 125°C | --   | --   | 1<br>10 | μA<br>μA |
| I <sub>GSSF</sub>                                      | Gate-Body Leakage Current, Forward                    | V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V                                                    | --   | --   | 100     | nA       |
| I <sub>GSSR</sub>                                      | Gate-Body Leakage Current, Reverse                    | V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V                                                   | --   | --   | -100    | nA       |
| On Characteristics                                     |                                                       |                                                                                                |      |      |         |          |
| V <sub>GS(th)</sub>                                    | Gate Threshold Voltage                                | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                     | 3.0  | --   | 5.0     | V        |
| R <sub>DS(on)</sub>                                    | Static Drain-Source On-Resistance                     | V <sub>GS</sub> = 10V, I <sub>D</sub> = 8A                                                     | --   | 0.31 | 0.38    | Ω        |
| g <sub>FS</sub>                                        | Forward Transconductance                              | V <sub>DS</sub> = 40V, I <sub>D</sub> = 8A                                                     | --   | 23   | --      | S        |
| Dynamic Characteristics                                |                                                       |                                                                                                |      |      |         |          |
| C <sub>iss</sub>                                       | Input Capacitance                                     | V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz                                     | --   | 1495 | 1945    | pF       |
| C <sub>oss</sub>                                       | Output Capacitance                                    |                                                                                                | --   | 235  | 310     | pF       |
| C <sub>rss</sub>                                       | Reverse Transfer Capacitance                          |                                                                                                | --   | 20   | 30      | pF       |
| Switching Characteristics                              |                                                       |                                                                                                |      |      |         |          |
| t <sub>d(on)</sub>                                     | Turn-On Delay Time                                    | V <sub>DD</sub> = 250V, I <sub>D</sub> = 16A<br>R <sub>G</sub> = 25Ω<br><br>(Note 4)           | --   | 40   | 90      | ns       |
| t <sub>r</sub>                                         | Turn-On Rise Time                                     |                                                                                                | --   | 150  | 310     | ns       |
| t <sub>d(off)</sub>                                    | Turn-Off Delay Time                                   |                                                                                                | --   | 65   | 140     | ns       |
| t <sub>f</sub>                                         | Turn-Off Fall Time                                    |                                                                                                | --   | 80   | 170     | ns       |
| Q <sub>g</sub>                                         | Total Gate Charge                                     | V <sub>DS</sub> = 400V, I <sub>D</sub> = 16A<br>V <sub>GS</sub> = 10V<br><br>(Note 4)          | --   | 32   | 45      | nC       |
| Q <sub>gs</sub>                                        | Gate-Source Charge                                    |                                                                                                | --   | 8.5  | --      | nC       |
| Q <sub>gd</sub>                                        | Gate-Drain Charge                                     |                                                                                                | --   | 14   | --      | nC       |
| Drain-Source Diode Characteristics and Maximum Ratings |                                                       |                                                                                                |      |      |         |          |
| I <sub>S</sub>                                         | Maximum Continuous Drain-Source Diode Forward Current |                                                                                                | --   | --   | 9.2     | A        |
| I <sub>SM</sub>                                        | Maximum Pulsed Drain-Source Diode Forward Current     |                                                                                                | --   | --   | 37      | A        |
| V <sub>SD</sub>                                        | Drain-Source Diode Forward Voltage                    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 16A                                                     | --   | --   | 1.4     | V        |
| t <sub>rr</sub>                                        | Reverse Recovery Time                                 | V <sub>GS</sub> = 0V, I <sub>S</sub> = 16A<br>dI <sub>F</sub> /dt = 100A/μs                    | --   | 490  | --      | ns       |
| Q <sub>rr</sub>                                        | Reverse Recovery Charge                               |                                                                                                | --   | 5.0  | --      | μC       |

### NOTES:

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2. L = 5.5 mH, I<sub>AS</sub> = 16 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.
3. I<sub>SD</sub> ≤ 16 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C.
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

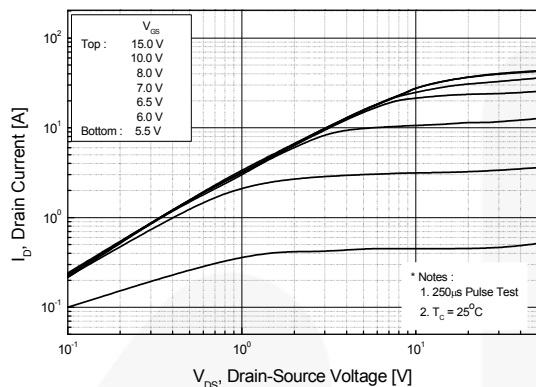


Figure 2. Transfer Characteristics

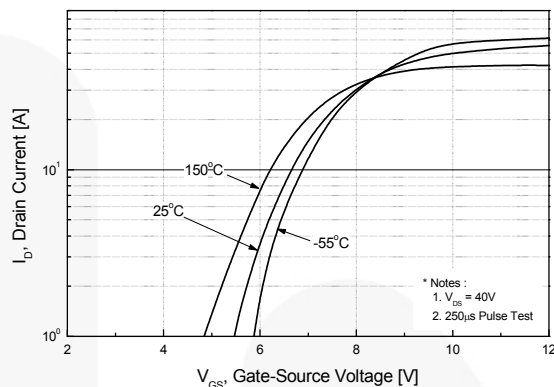


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

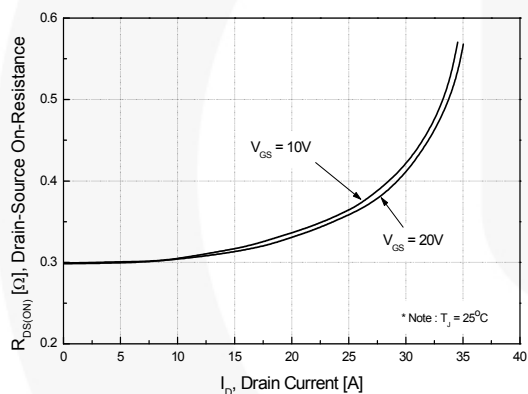


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

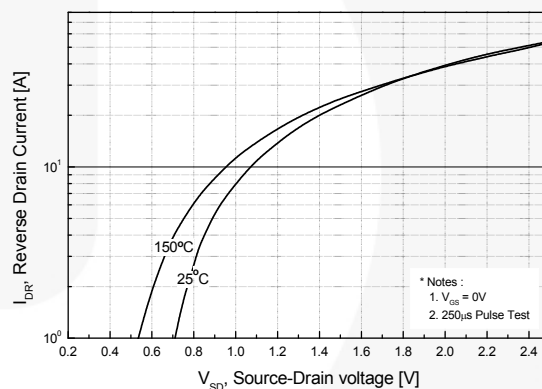


Figure 5. Capacitance Characteristics

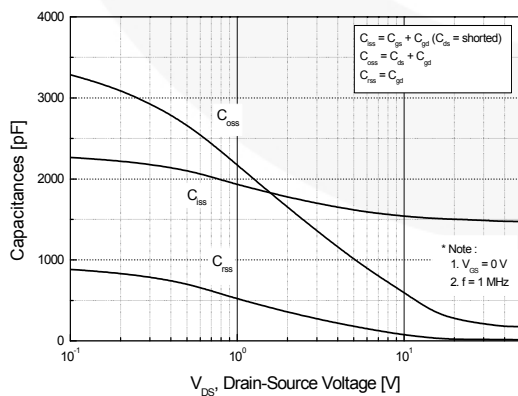
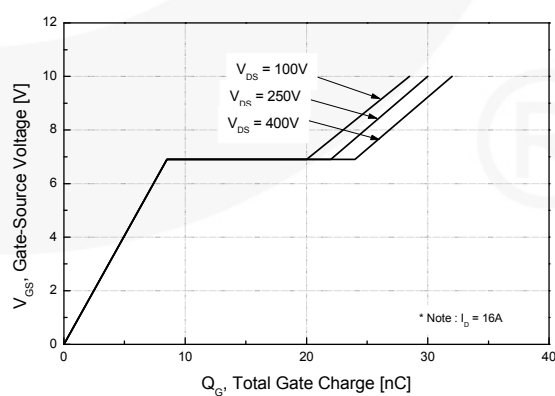
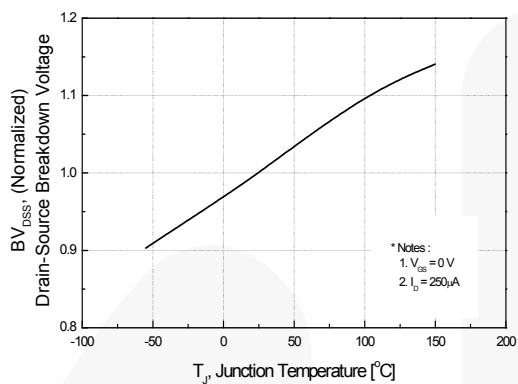


Figure 6. Gate Charge Characteristics

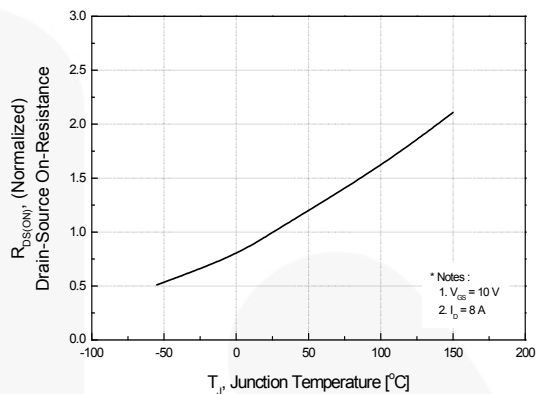


# Typical Performance Characteristics (Continued)

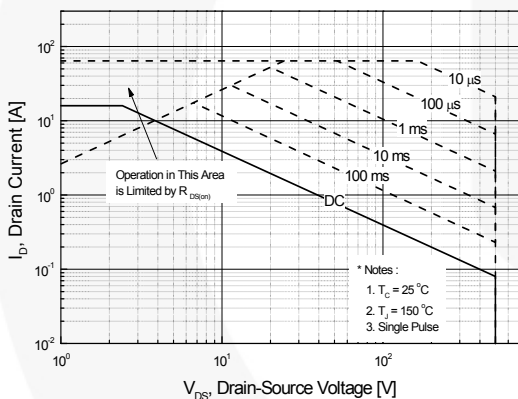
**Figure 7. Breakdown Voltage Variation vs. Temperature**



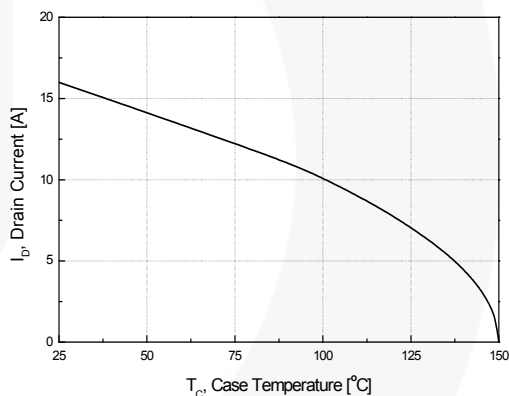
**Figure 8. On-Resistance Variation vs. Temperature**



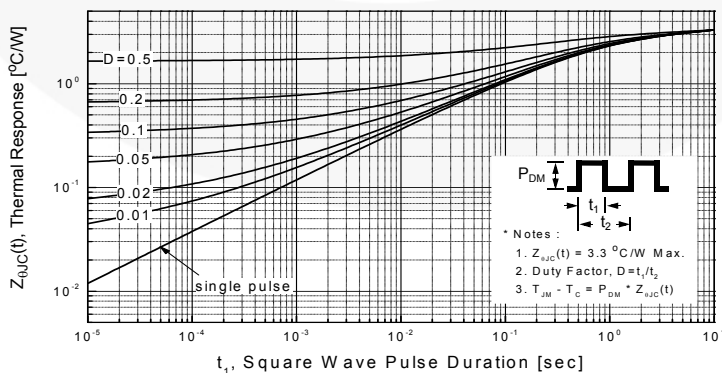
**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. Transient Thermal Response Curve**



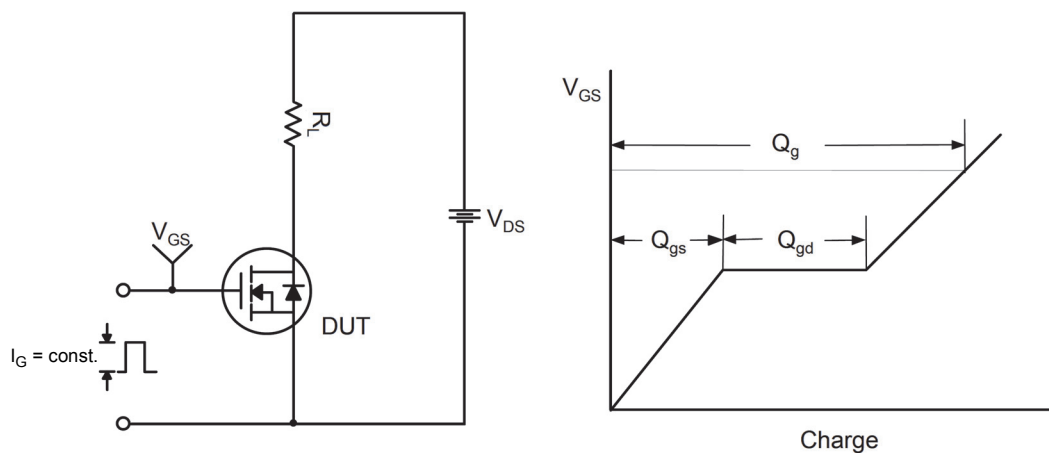


Figure 12. Gate Charge Test Circuit & Waveform

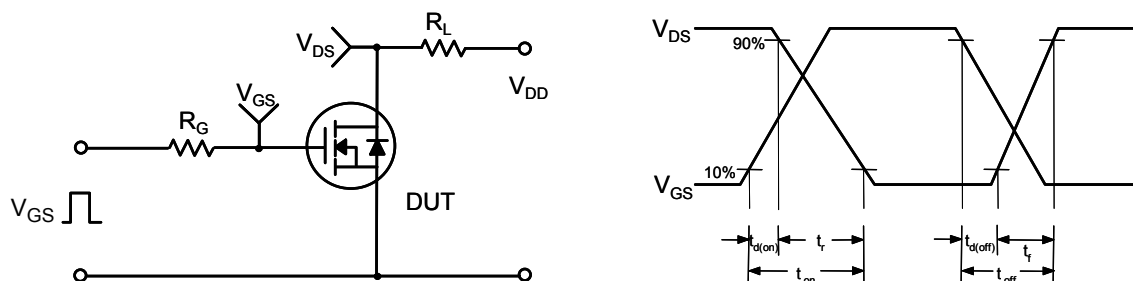


Figure 13. Resistive Switching Test Circuit & Waveforms

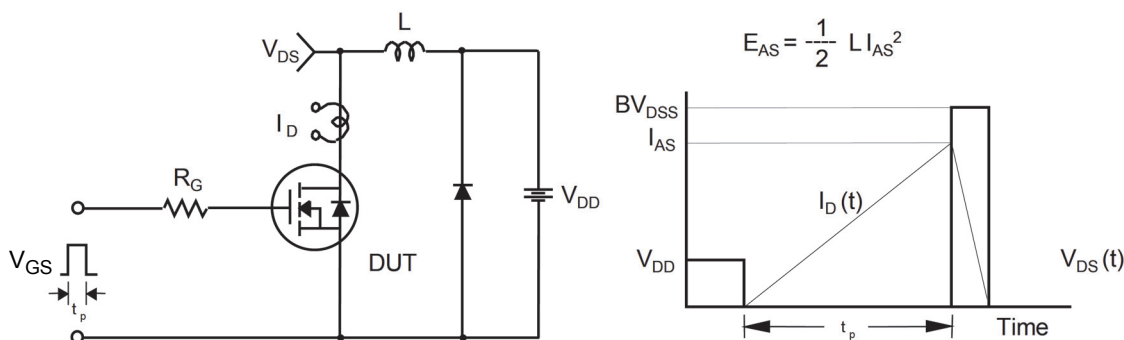


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

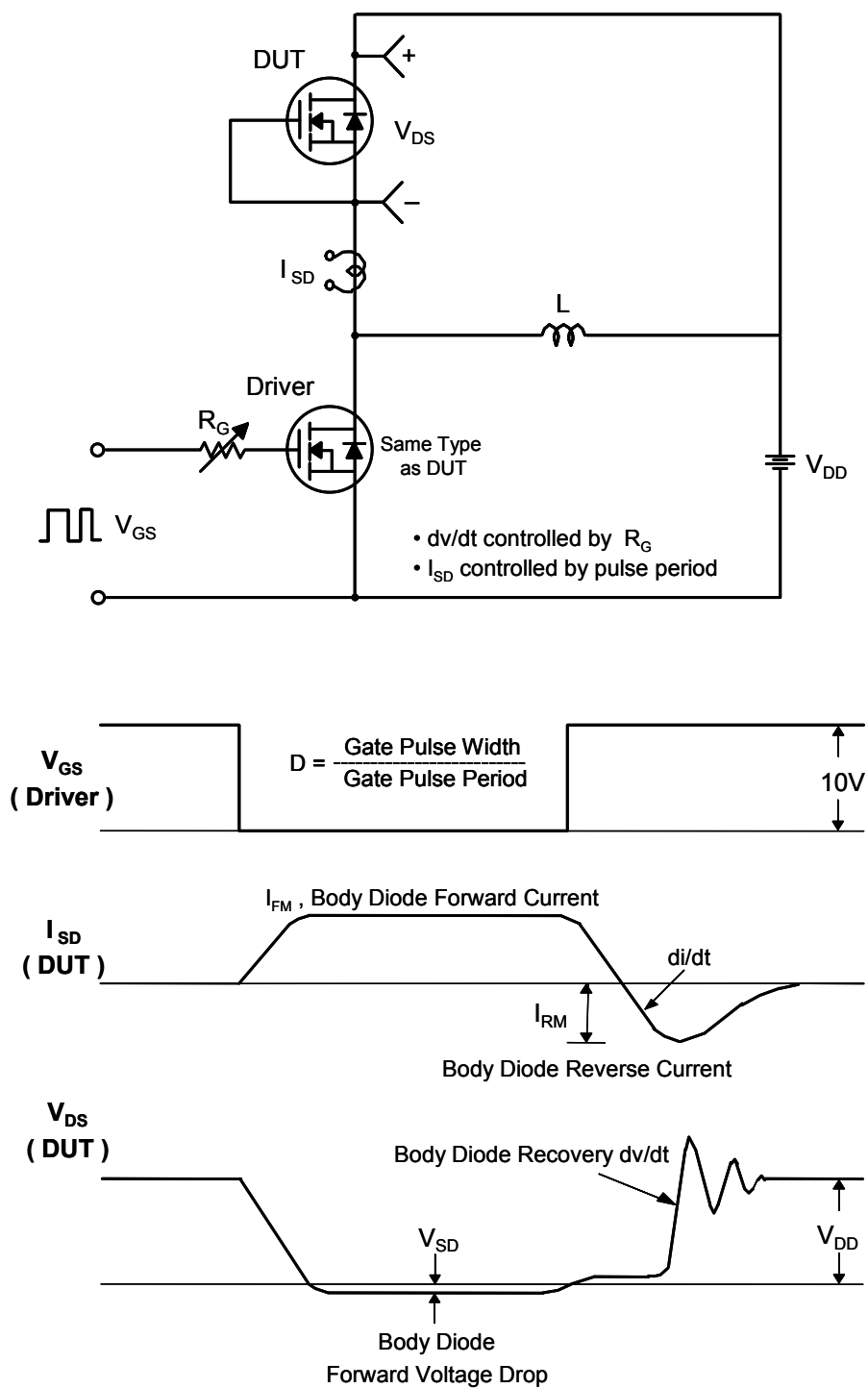
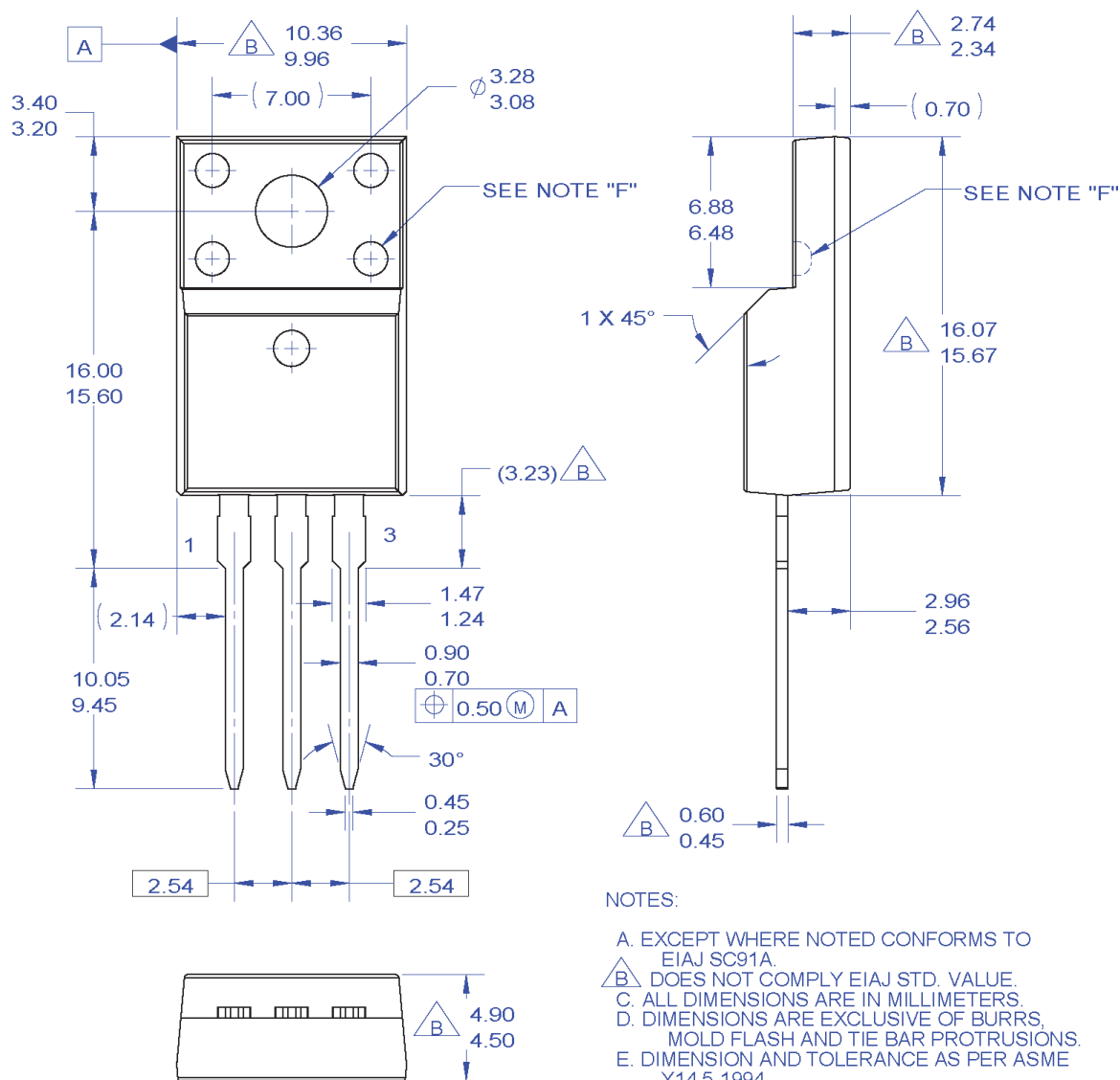


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

# Mechanical Dimensions



**Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead**

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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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